

Electrical Characteristics (T_j = 25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV_{DSS}	30	-	-	V	$V_{GS}=0, I_D=250\mu A$
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS} / \Delta T_j$	-	0.03	-	V/°C	Reference to 25°C, $I_D=1mA$
Gate Threshold Voltage	$V_{GS(th)}$	1.0	-	3.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Forward Transconductance	g_{fs}	-	25	-	S	$V_{DS}=10V, I_D=10A$
Gate-Source Leakage Current	I_{GSS}	-	-	±100	nA	$V_{GS}= \pm 20V$
Drain-Source Leakage Current(T _j =25°C)	I_{DSS}	-	-	1	uA	$V_{DS}=30V, V_{GS}=0$
Drain-Source Leakage Current(T _j =175°C)		-	-	250	uA	$V_{DS}=24V, V_{GS}=0$
Static Drain-Source On-Resistance ²	$R_{DS(ON)}$	-	-	12	mΩ	$V_{GS}=10V, I_D=20A$
		-	-	25		$V_{GS}=4.5V, I_D=15A$
Total Gate Charge ²	Q_g	-	11.6	19	nC	$I_D=20A$ $V_{DS}=24V$ $V_{GS}=4.5V$
Gate-Source Charge	Q_{gs}	-	3.9	-		
Gate-Drain ("Miller") Charge	Q_{gd}	-	7	-		
Turn-on Delay Time ²	$T_{d(on)}$	-	8.8	-	ns	$V_{DS}=15V$ $I_D=20A$ $V_{GS}=10V$ $R_G=3.3\Omega$ $R_D=0.75\Omega$
Rise Time	T_r	-	57.5	-		
Turn-off Delay Time	$T_{d(off)}$	-	18.5	-		
Fall Time	T_f	-	6.4	-		
Input Capacitance	C_{iss}	-	1135	1816	pF	$V_{GS}=0V$ $V_{DS}=25V$ $f=1.0MHz$
Output Capacitance	C_{oss}	-	200	-		
Reverse Transfer Capacitance	C_{rss}	-	135	-		

Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward On Voltage ²	V_{SD}	-	-	1.3	V	$I_S=45A, V_{GS}=0V$
Reverse Recovery Time ²	T_{rr}	-	23.3	-	ns	$I_S=20A, V_{GS}=0V$ $di/dt=100A/\mu s$
Reverse Recovery Charge	Q_{rr}	-	16	-	nC	

Notes: 1. Pulse width limited by safe operating area.

2. Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

Characteristics Curve

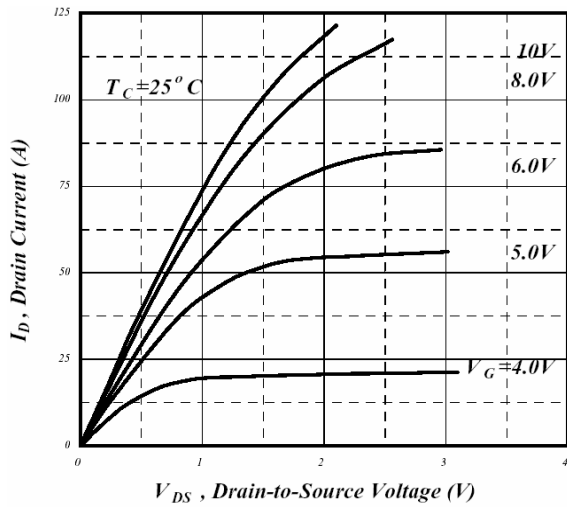


Fig 1. Typical Output Characteristics

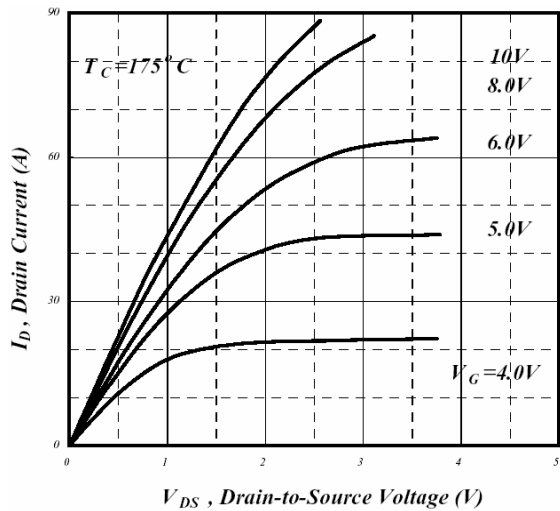


Fig 2. Typical Output Characteristics

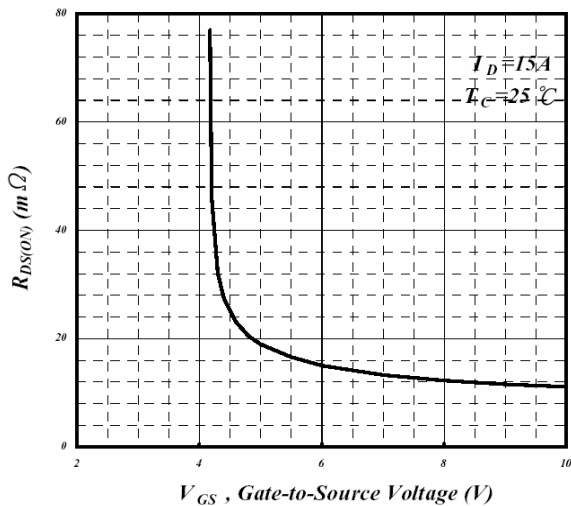


Fig 3. On-Resistance v.s. Gate Voltage

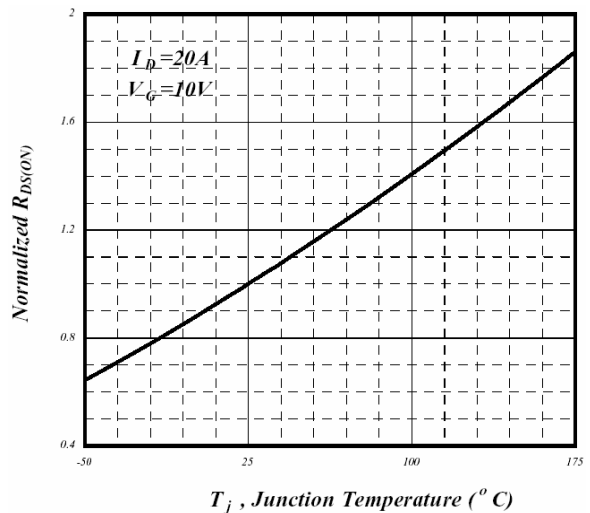


Fig 4. Normalized On-Resistance v.s. Junction Temperature

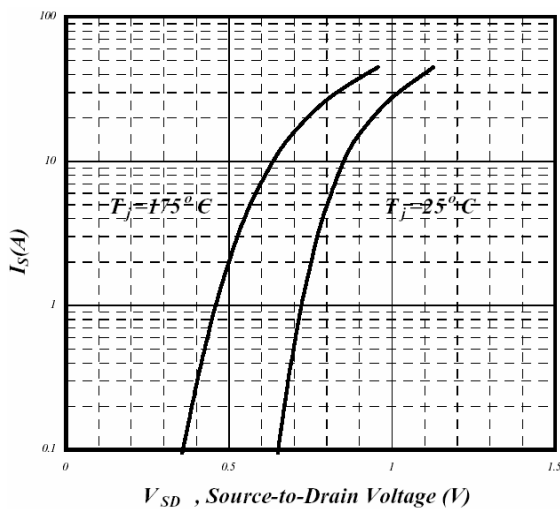


Fig 5. Forward Characteristics of Reverse Diode

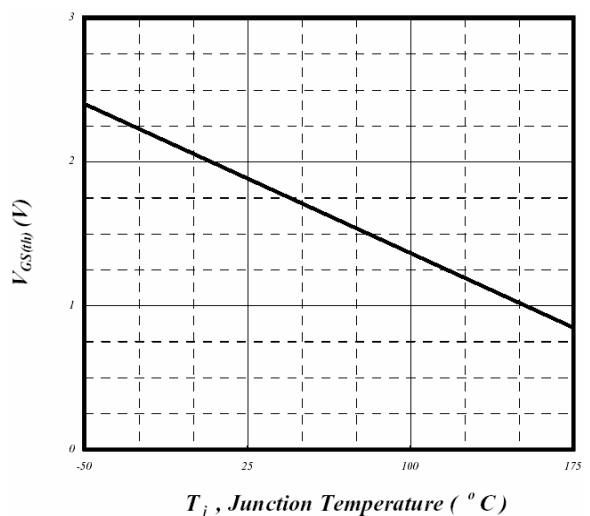


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

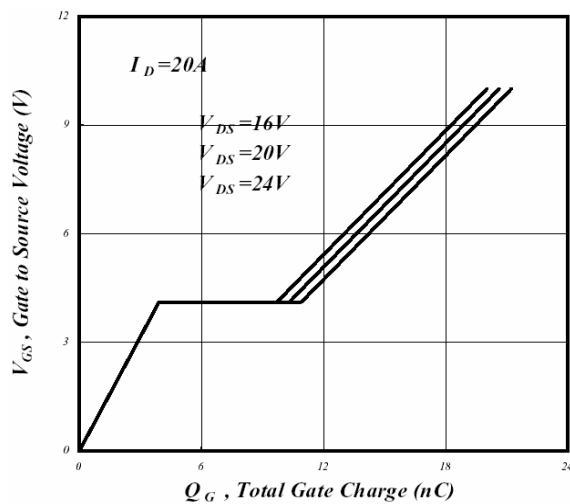


Fig 7. Gate Charge Characteristics

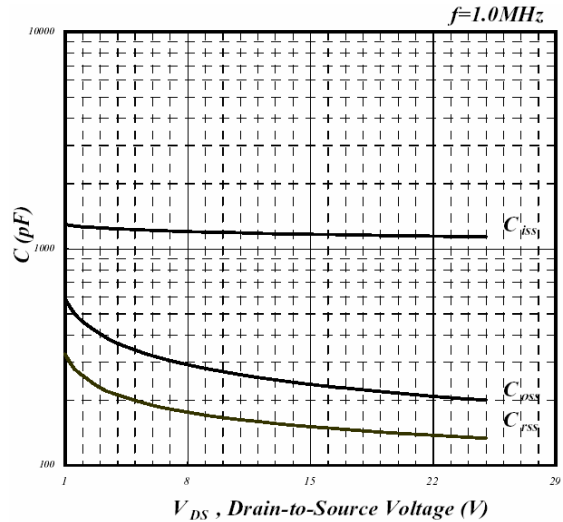


Fig 8. Typical Capacitance Characteristics

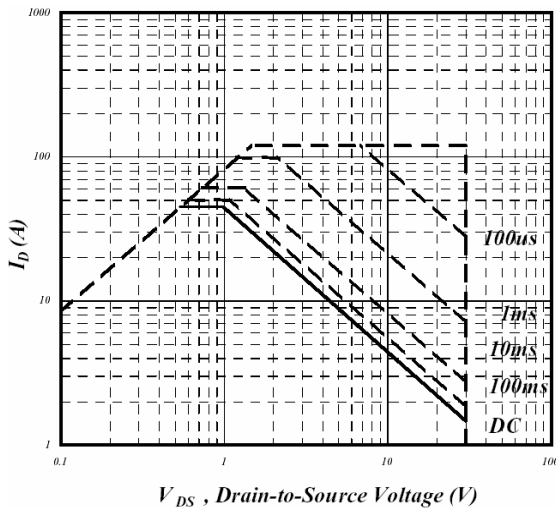


Fig 9. Maximum Safe Operating Area

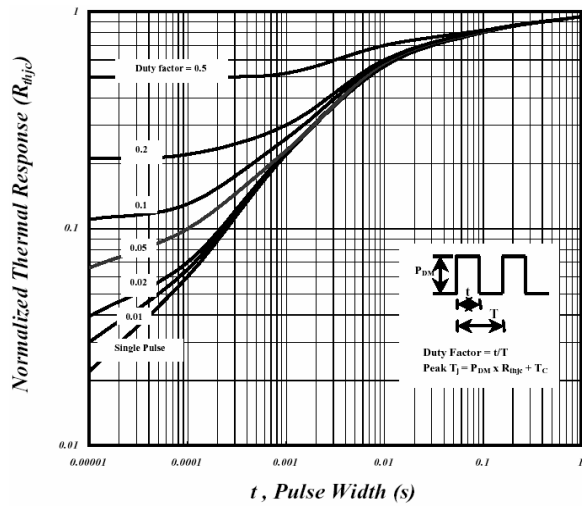


Fig 10. Effective Transient Thermal Impedance

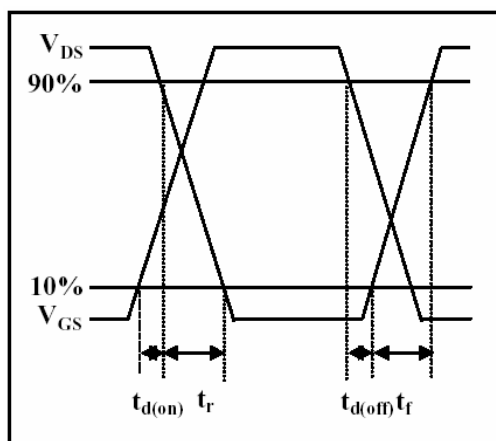


Fig 11. Switching Time Waveform

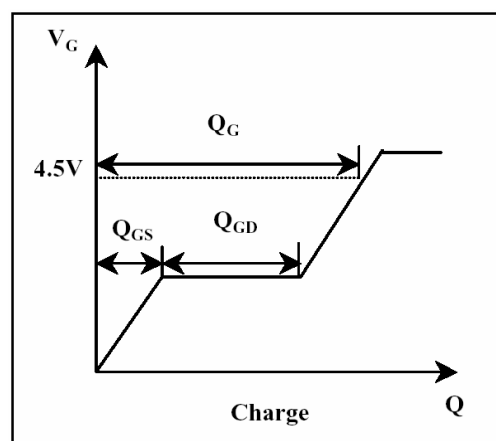


Fig 12. Gate Charge Waveform

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